

## IFN6449, IFN6450

## N-Channel Silicon Junction Field-Effect Transistor

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## • High Voltage

Absolute maximum ratings at  $T_A = 25^\circ\text{C}$ 

	IFN6449	IFN6450
Reverse Gate Source Voltage	- 100 V	- 100 V
Reverse Gate Drain Voltage	- 300 V	- 200 V
Continuous Forward Gate Current	10 mA	10 mA
Continuous Device Power Dissipation	800 mW	800 mW
Power Derating	6.4 mW/°C	6.4 mW/°C

At  $25^\circ\text{C}$  free air temperature:

## Static Electrical Characteristics

		IFN6449		IFN6450		Unit	Process NJ42	
		Min	Max	Min	Max		Test Conditions	
Gate Drain Breakdown Voltage	$V_{(BR)GDO}$	- 300		- 200		V	$I_G = - 10 \mu\text{A}$ , $I_S = \emptyset\text{A}$	
Gate Source Breakdown Voltage	$V_{(BR)GSO}$	- 100		- 100		V	$I_G = - 10 \mu\text{A}$ , $I_D = \emptyset\text{A}$	
Gate Reverse Current	$I_{GSS}$				- 100	nA	$V_{GS} = - 80\text{V}$ , $V_{DS} = \emptyset\text{V}$	
					- 100	$\mu\text{A}$	$V_{GS} = - 80\text{V}$ , $V_{DS} = \emptyset\text{V}$	$T_A = 150^\circ\text{C}$
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	- 2	- 15	- 2	- 15	V	$V_{DS} = 30\text{V}$ , $I_D = 4 \text{ nA}$	
Drain Saturation Current (Pulsed)	$I_{DSS}$	2	10	2	10	mA	$V_{DS} = 30\text{V}$ , $V_{GS} = \emptyset\text{V}$	

## Dynamic Electrical Characteristics

Common Source Forward Transfer Transmittance	$ Y_{fs} $	0.5	3	0.5	3	mS	$V_{DS} = 30\text{V}$ , $V_{GS} = \emptyset\text{V}$	$f = 1 \text{ kHz}$
Common Source Output Conductance	$g_{os}$		100		100	$\mu\text{S}$	$V_{DS} = 30\text{V}$ , $V_{GS} = \emptyset\text{V}$	$f = 1 \text{ kHz}$
Common Source Input Capacitance	$C_{iss}$		10		10	pF	$V_{DS} = 30\text{V}$ , $V_{GS} = \emptyset\text{V}$	$f = 1 \text{ MHz}$
Common Source Reverse Transfer Capacitance	$C_{rss}$		5		5	pF	$V_{DS} = 30\text{V}$ , $V_{GS} = \emptyset\text{V}$	$f = 1 \text{ MHz}$

## TO-39 Package

Dimensions in Inches (mm)

## Pin Configuration

1 Source, 2 Drain, 3 Gate &amp; Case



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